

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Previously Presented) A semiconductor device comprising:
a plurality of first bump electrodes arranged on a main surface, and each of said plurality of first bump electrodes receiving signals or power;
a plurality of dummy bump electrodes arranged on said main surface, and each of said plurality of dummy bump electrodes electrically connected to an associated one of said plurality of first bump electrodes wherein said plurality of dummy bump electrodes and said plurality of first bump electrodes being arranged alternately along to circumference of bump group.
2. (Previously Presented) The semiconductor device as claimed in claim 1 further comprising:
a plurality of protection circuits electrically coupled to said plurality of first bump electrodes.
3. (Original) The semiconductor device as claimed in claim 1, further comprising:
a plurality of test electrodes electrically connected to said first bump electrodes.
4. (Original) The semiconductor device as claimed in claim 3, wherein
said plurality of test electrodes being arranged along four edges of said semiconductor device.
5. (Previously Presented) The semiconductor device as claimed in claim 1, wherein
said plurality of dummy bump electrodes being higher than a plurality of chip electrodes.
6. (Original) The semiconductor device as claimed in claim 1, wherein said plurality of dummy bump electrodes being arranged closer than said plurality of first bump electrodes.
7. (Previously Presented) The semiconductor device as claimed in claim 1, wherein
said plurality of dummy bump electrodes being arranged between said plurality of first bump electrodes and a plurality of chip electrodes.

8. (Original) The semiconductor device as claimed in claim 1, wherein said plurality of dummy bump electrodes being provided for relaxation of stress at mounting said semiconductor device.

9.-11. (Cancelled)

12. (Currently Amended) A device comprising:
a substrate;
an insulating layer formed above said substrate;
a ~~plurality of pads~~ pad formed above said insulating layer, and said pad receiving a signal;
~~a plurality of external bump electrodes~~ an external bump electrode formed above said insulating layer, and ~~[[each]] electrically connected to said pad an associated one of said plurality of pads~~; and
a dummy bump electrode formed above said insulating layer, and connected to said external bump electrode ~~associated one of said plurality of external bump electrodes~~.

13. (Currently Amended) The device as claimed in claim 12, wherein said dummy bump electrode being allocated between said pad ~~an associated one of said plurality of pads~~ and said external bump electrode ~~an associated one of said plurality of external bump electrodes~~.

14. (Currently Amended) The device as claimed in claim 12, wherein said pad ~~plurality of pads~~ being allocated along an edge of said substrate.

15. (Currently Amended) The device as claimed in claim 13, wherein said pad ~~plurality of pads~~ being allocated along an edge of said substrate.

16. (Currently Amended) The device as claimed in claim 12, further comprising a first wiring connected between said pad ~~an associated one of said plurality of pads~~ and said external bump electrode ~~an associated one of said plurality of external bump electrodes~~, and a second wiring connected between said external bump electrode ~~an associated one of said plurality of external bump electrodes~~ and said dummy bump electrode.

17. (Currently Amended) The device as claimed in claim 12, wherein said pad is plurality of pads are coupled to an internal circuit.

18. (Currently Amended) The device as claimed in claim 12, wherein said pad is plurality of pads are coupled to a plurality of input/output buffers.

19. (Currently Amended) A semiconductor device comprising:
a pad formed above a semiconductor chip;
an external [[a first]] bump electrode formed above said semiconductor chip
corresponding to said pad;

a dummy bump electrode formed above said semiconductor chip ~~between said first bump electrode and said pad~~;

a first wiring connected between said external [[first]] bump electrode and said dummy bump electrode [[pad]]; and

a second wiring connected between a center of said first wiring ~~said dummy electrode~~
or a portion near to said external [[first]] bump electrode from said [[a]] center of said first wiring and said pad.

20. (Currently Amended) The semiconductor device as claimed in claim [[19]] 22, wherein said dummy bump electrode is arranged in a [[first]] direction along a side of said semiconductor chip.

21. (Currently Amended) The semiconductor device as claimed in claim [[19]] 22, wherein said external [[first]] bump electrode is arranged internally from a side of said semiconductor chip relative to said dummy bump electrode.

22. (New) The semiconductor device as claimed in claim 19, wherein said dummy bump electrode is formed between said external bump electrode and said pad.

23. (New) The semiconductor device as claimed in claim 19, wherein said external bump electrode receives a signal through said pad.

24. (New) A semiconductor device comprising:

a semiconductor chip;

a first pad formed above said semiconductor chip;

a second pad formed above said semiconductor chip;

a first external bump electrode above said semiconductor, and connected to said first pad;

a second external bump electrode above said semiconductor, and connected to said second pad;

a first dummy bump electrode above said semiconductor, and connected to said first external bump electrode; and

a second dummy bump electrode above said semiconductor, and connected to said second external bump electrode.

25. (New) The semiconductor device as claimed in claim 24, wherein said first dummy bump electrode is formed between said first pad and said first external bump electrode, and said second dummy bump electrode is formed between said second pad and said second external bump electrode.

26. (New) The semiconductor device as claimed in claim 24, wherein said first external bump electrode receives a first signal through said first pad, and said second external bump electrode receives a second signal through said second pad.